

Proposed Amendment of Specification

U.S. Patent Application Serial No. 10/820,781

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Our Reference: US7099

In the paragraph [0024] and [0025] of page 16, and [0080] of page 31 in the specification,
Please amend as follows:

[0024]

In the case of irradiating ~~the uniform region in~~ the laser beam uniformly, that is, scanning the laser beam at constant speed, the element-forming region in the irradiated object can be irradiated and thus uniform irradiation method of the laser beam can be provided according to the present invention.

[0025]

Moreover, when a semiconductor film is used as the irradiated object, it is possible to provide the poly-crystalline TFT having uniform crystallinity and uniform electric characteristic. With such a poly-crystalline TFT equipped, advantageous effects such as uniformity of the display and enhancement of the performance can be expected in a liquid crystal display device, a display device such as a light-emitting device having a self light-emitting element and an integrated circuit having a CPU and a memory.

[0080]

In addition, the organic compound layer 405 is formed by a vapor deposition method or a coating method. In this embodiment mode, the organic compound layer is formed in a vapor deposition apparatus to obtain uniform film thickness. In order to enhance the reliability, it is preferable to degas by means of vacuum heating (at a temperature ranging from 100 to 250°C) just before forming the organic compound layer 405. For example, when the vapor deposition method is used, the film is deposited in the film-forming chamber that is vacuum pumped so that the degree of vacuum is 5×10^{-3} Torr (0.665 Pa) or less, preferably in the range of 10^{-4} to 10^{-6} Pa Torr. At the deposition, the organic compound is vaporized by heating it in advance, and it is spattered toward the substrate by opening the shutter. Vaporized organic compound is spattered upward and deposited through an opening provided in a metal mask.